

IN THE CLAIMS:

Please amend the claims as follows:

Claim 1. (Previously Amended) A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

fig. 1
each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with said gate insulating film and top and side surfaces of said first conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

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a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein a portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein a portion which said second conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 2. (Previously Added). A ferroelectric liquid crystal display device according to claim 1, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 3. (Previously Added). A ferroelectric liquid crystal display device according to claim 1, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 4. (Previously Added). A ferroelectric liquid crystal display device according to claim 1, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 5. (Canceled).

Claim 6. (Previously Amended) A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with said gate insulating film and top and side surfaces of said first conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein a portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein the portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT does not overlap said first source and drain regions;

wherein a portion which said second conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 7. (Previously Added). A ferroelectric liquid crystal display device according to claim 6, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 8. (Previously Added). A ferroelectric liquid crystal display device according to claim 6, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 9. (Previously Added). A ferroelectric liquid crystal display device according to claim 6, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 10. (Canceled).

Claim 11. (Previously Amended) A ferroelectric liquid crystal display device having an n-

channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

a first gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a pair of LDD regions and first source and drain regions;

wherein said first gate electrode partially overlaps said pair of LDD regions,

and

said p-channel TFT comprising:

a second gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film interposed therebetween, said second semiconductor layer comprising a second channel formation region and second source and drain regions being in contact with said second channel formation region,

wherein said second gate electrode partially overlaps said second source and drain regions, and

wherein a wiring is connected to at least one of said second source and drain regions.

Claim 12. (Previously Amended). A ferroelectric liquid crystal display device according to claim 11, wherein said first and second gate electrodes comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 13. (Canceled).

Claim 14. (Previously Amended) A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with said gate insulating film and top and side surfaces of said first conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein a portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein a portion which said second conductive layer is in contact with said gate insulating film in said p-channel TFT is partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 15. (Previously Added). A goggle type display device according to claim 14, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 16. (Previously Added). A goggle type display device according to claim 14, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 17. (Previously Added). A goggle type display device according to claim 14, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 18. (Canceled).

Claim 19. (Previously Amended) A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with said gate insulating film and top and side surfaces of said first conductive layer;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a pair of LDD regions and first source and drain regions; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and second source and drain regions,

wherein a portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT partially overlaps said pair of LDD regions;

wherein the portion which said second conductive layer is in contact with said gate insulating film in said n-channel TFT does not overlap said first source and drain regions;

wherein a portion which said second conductive layer is in contact with said gate insulating film in said p-channel TFT partially overlaps said second source and drain regions,

wherein said semiconductor layer of said p-channel TFT has no LDD regions.

Claim 20. (Previously Added). A goggle type display device according to claim 19, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

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Claim 21. (Previously Added). A goggle type display device according to claim 19, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises a single layer or a plurality of layers.

Claim 22. (Previously Added). A goggle type display device according to claim 19, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 23. (Canceled).

Claim 24. (Currently Amended) A goggle type display device having an n-channel TFT and a p-channel TFT over a substrate,

figs. 1, 15D
said n-channel TFT comprising:

a first gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first

channel formation region, a pair of LDD regions and first source and drain regions;

wherein said first gate electrode partially overlaps said pair of LDD regions,

and

said p-channel TFT comprising:

a second gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film interposed therebetween, said second semiconductor layer comprising a second channel formation region and second source and drain regions being in contact with said second channel formation region,

wherein said second gate electrode partially overlaps said second source and drain regions, and

wherein a wiring is connected to said at least one of said second source and drain regions.

Claim 25. (Previously Amended). A goggle type display device according to claim 24, wherein said first and second gate electrodes comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Claim 26. (Canceled).